

# *Etched In Time, Inc.*

Since 1983

## **LPS 2500 RF Linear Source Process Results**

- **High Speed Process (SF6+He)**
- Rate: 5035 angstroms/min Uniformity 2.8% 1 sigma
- **Medium Speed Process (SF6+He)**
- Rate: 2917 angstroms/min: Uniformity 1.7% 1 sigma
- **Low Speed Process (SF6+He)**
- Rate: 1009 angstroms/min: Uniformity 1.9% 1 sigma
- **High Selectivity Process (SF6+He+CHF3)**
- Rate: 2022 angstroms/min: Uniformity 3.1% 1 sigma
- **SiO<sub>2</sub>: Photoresist Selectivity: 3.5:1**
- Sidewall slope: 82 degrees with no undercut of oxide